

General Description

The DMN2040LTS-13 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gatecharge for most of the small power switching and load switch applications. The meet the RoHS and Product requirement with full function reliability approved.

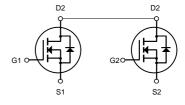


General Features

 $V_{DS} = 20V I_{D} = 6A$

 $R_{DS(ON)}$ < 27m Ω @ V_{GS}=4. 5V

 $R_{DS(ON)}$ <37m Ω @ V_{GS}=2. 5V



Application

Battery protection

Load switch

Uninterruptible power supply

Dual N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMN2040LTS-13	TSSOP-8	HXY MOSFET	5000

Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	20	V
V _G s	Gate-Source Voltage	±12	V
I _D	Drain Current-Continuous	6	А
Ірм	Drain Current-Pulsed (Note 1)	25	А
P _D	Maximum Power Dissipation	1.5	W
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	83	°C/W



Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	20	21	-	٧
Zero Gate Voltage Drain Current	Ipss	V _{DS} =19.5V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	lgss	V _{GS} =±10V,V _{DS} =0V	-	_	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.5	0.7	1.2	V
		V _{GS} =4.5V, I _D =4.5A	-	21	27	mΩ
Drain-Source On-State Resistance	Rds(on)	V _{GS} =2.5V, I _D =3.5A	-	27	37	mΩ
Forward Transconductance	grs	V _{DS} =5V,I _D =4.5A	-	10	-	S
Input Capacitance	C _{lss}		-	600	-	PF
Output Capacitance	Coss	V _{DS} =8V,V _{GS} =0V, F=1.0MHz	-	330	-	PF
Reverse Transfer Capacitance	Crss	F-1.UIVIDZ	-	140	-	PF
Turn-on Delay Time	td(on)		-	10	20	nS
Turn-on Rise Time	tr	V _{DD} =10V,I _D =1A	-	11	25	nS
Turn-Off Delay Time	td(off)	$V_{GS}=10V, N_{GEN}=12V$ $V_{GS}=4.5V, R_{GEN}=6\Omega$	-	35	70	nS
Turn-Off Fall Time	t _f		-	30	60	nS
Total Gate Charge	Qg		-	10	15	nC
Gate-Source Charge	Qgs	V _{DS} =10V,I _D =6A,	-	2.3	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =4.5V	-	1.5	-	nC
Diode Forward Voltage (Note 3)	VsD	V _{GS} =0V,I _S =1.7A	-	0.75	1.2	V
Diode Forward Current (Note 2)	Is		-	-	1.7	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Characteristics

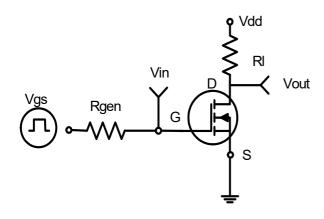


Figure 1:Switching Test Circuit

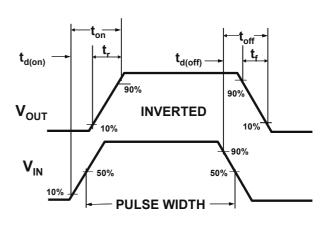


Figure 2:Switching Waveforms

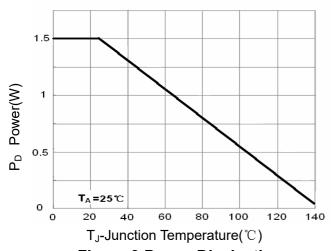
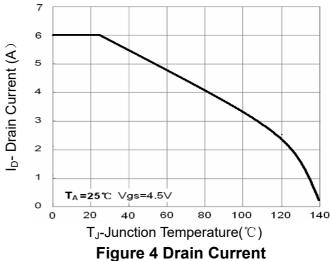


Figure 3 Power Dissipation



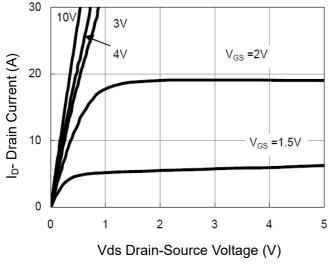


Figure 5 Output Characteristics

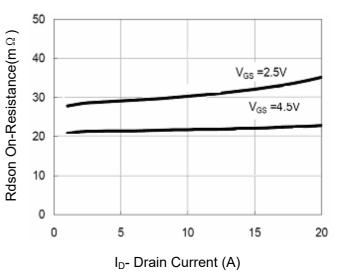


Figure 6 Drain-Source On-Resistance

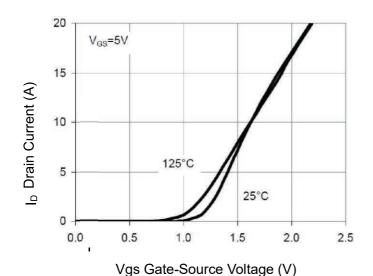
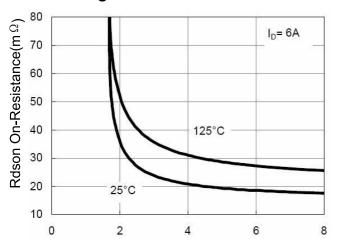


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

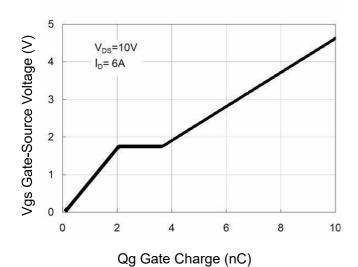
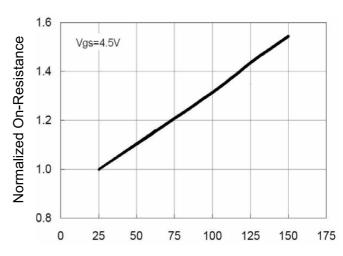
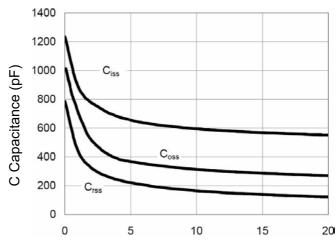


Figure 11 Gate Charge



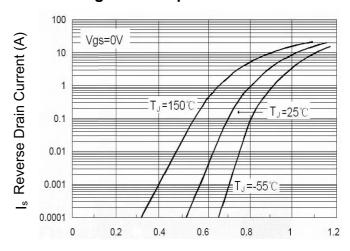
 $\mathsf{T}_{\mathsf{J}} ext{-}\mathsf{Junction}\;\mathsf{Temperature}({}^{\circ}\mathsf{C})$

Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward



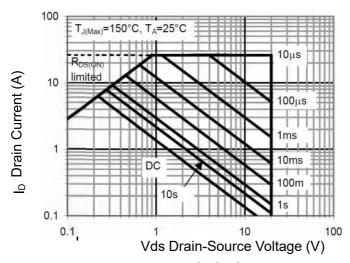
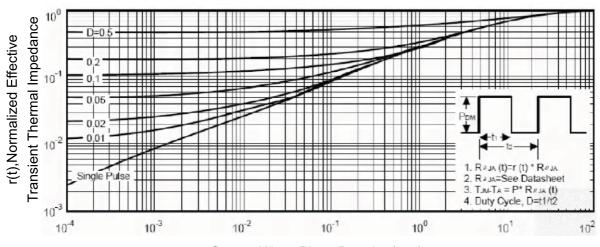


Figure 13 Safe Operation Area

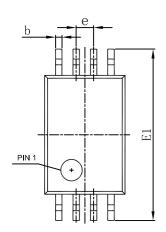


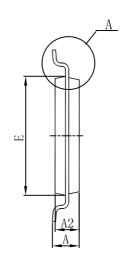
Square Wave Pluse Duration(sec)

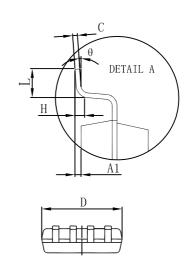
Figure 14 Normalized Maximum Transient Thermal Impedance



TSSOP-8 Package Outline Dimensions







Symbol	Dimensions 1	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max		
D	2.900	3. 100	0.114	0.122		
Е	4.300	4. 500	0. 169	0.177		
b	0.190	0.300	0.007	0.012		
С	0.090	0.200	0.004	0.008		
E1	6. 250	6. 550	0. 246	0.258		
A		1. 200		0.047		
A2	0.800	1.000	0.031	0.039		
A1	0.050	0.150	0.002	0.006		
e	0. 65	0.65 (BSC)		0. 026 (BSC)		
L	0.500	0.700	0.020	0.028		
Н	0.25(T	0.25(TYP)		0.01(TYP)		
θ	1°	7°	1°	7°		

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